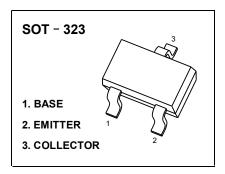


MMBT3904W TRANSISTOR(NPN)

for switching and amplifier applications



MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	60	V
Collector Emitter Voltage	V _{CEO}	40	V
Emitter Base Voltage	V _{EBO}	6	V
Collector Current	Ι _c	200	mA
Total Power Dissipation	P _{tot}	200	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C



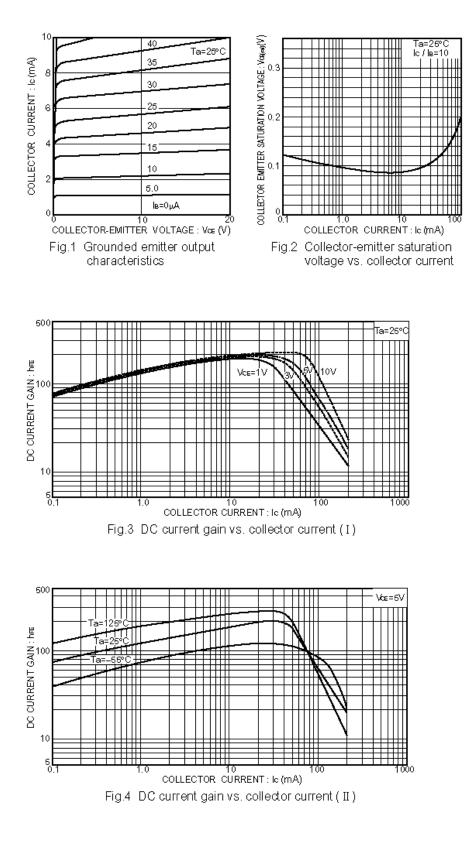
ELECTRICAL CHARACTERISTICS (Ta=25 $^{\circ}$ C unless otherwise specified)

Parameter	Symbol	Min.	Max.	Unit
$ \begin{array}{l} \text{DC Current Gain} \\ \text{at } V_{\text{CE}} = 1 \ \text{V}, \ \text{I}_{\text{C}} = 0.1 \ \text{mA} \\ \text{at } V_{\text{CE}} = 1 \ \text{V}, \ \text{I}_{\text{C}} = 1 \ \text{mA} \\ \text{at } V_{\text{CE}} = 1 \ \text{V}, \ \text{I}_{\text{C}} = 10 \ \text{mA} \\ \text{at } V_{\text{CE}} = 1 \ \text{V}, \ \text{I}_{\text{C}} = 50 \ \text{mA} \\ \text{at } V_{\text{CE}} = 1 \ \text{V}, \ \text{I}_{\text{C}} = 100 \ \text{mA} \\ \end{array} $	h _{FE} h _{FE} h _{FE} h _{FE}	40 70 100 60 30	- - 300 - -	- - - -
Collector Emitter Cutoff Current at $V_{CE} = 30 V$	I _{CES}	-	50	nA
Emitter Base Cutoff Current at $V_{EB} = 3 V$	I _{EBO}	-	50	nA
Collector Base Breakdown Voltage at $I_c = 10 \ \mu A$	V _{(BR)CBO}	60	-	V
Collector Emitter Breakdown Voltage at $I_c = 1 \text{ mA}$	V _{(BR)CEO}	40	-	V
Emitter Base Breakdown Voltage at $I_E = 10 \ \mu A$	V _{(BR)EBO}	6	-	V
Collector Emitter Saturation Voltage at $I_c = 10 \text{ mA}$, $I_B = 1 \text{ mA}$ at $I_c = 50 \text{ mA}$, $I_B = 5 \text{ mA}$	V _{CE(sat)}	-	0.2 0.3	V
Base Emitter Saturation Voltage at $I_c = 10 \text{ mA}$, $I_B = 1 \text{ mA}$ at $I_c = 50 \text{ mA}$, $I_B = 5 \text{ mA}$	V _{BE(sat)}	0.65 -	0.85 0.95	V
Transition Frequency at $V_{CE} = 20 \text{ V}$, $-I_E = 10 \text{ mA}$, f = 100 MHz	f _T	300	-	MHz
Collector Output Capacitance at $V_{CB} = 10 \text{ V}$, f = 100 KHz	C _{ob}	-	4	pF
Delay Time at $V_{CC} = 3 \text{ V}$, $V_{BE(OFF)} = 0.5 \text{ V}$, $I_C = 10 \text{ mA}$, $I_{B1} = 1 \text{ mA}$	t _d	-	35	ns
Rise Time at $V_{CC} = 3 \text{ V}$, $V_{BE(OFF)} = 0.5 \text{ V}$, $I_C = 10 \text{ mA}$, $I_{B1} = 1 \text{ mA}$	t _r	-	35	ns
Storage Time at $V_{CC} = 3 \text{ V}$, $I_C = 10 \text{ mA}$, $I_{B1} = -I_{B2} = 1 \text{ mA}$	t _{stg}	-	200	ns
Fall Time at $V_{CC} = 3 \text{ V}$, $I_C = 10 \text{ mA}$, $I_{B1} = -I_{B2} = 1 \text{ mA}$	t _f	-	50	ns



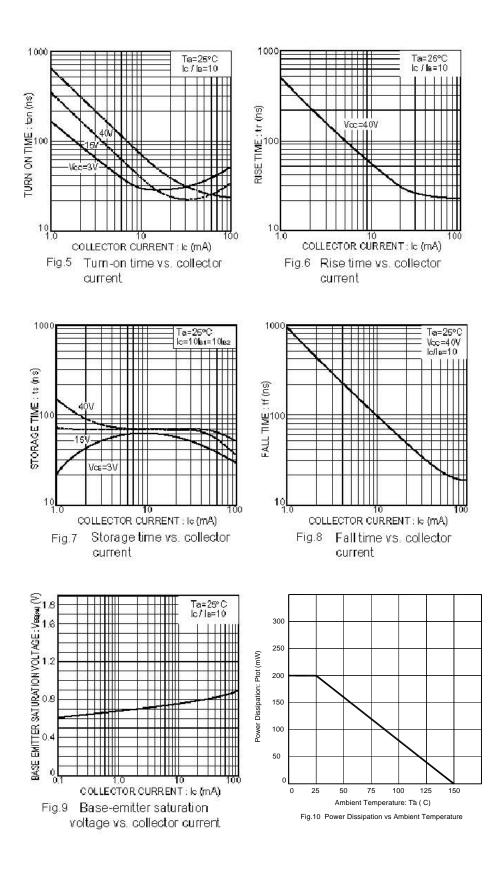
MMBT3904W

TYPICAL CHARACTERISTICS



MMBT3904W

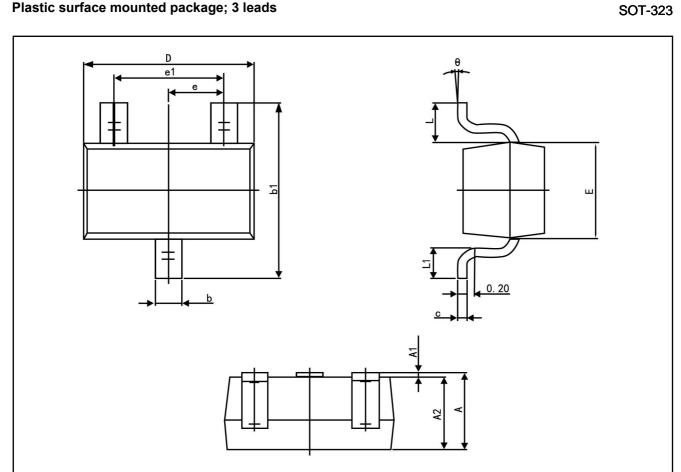






PACKAGE OUTLINE

Plastic surface mounted package; 3 leads



Symbol	Dimension in Millimeters		
Symbol -	Min	Max	
А	0.900	1.100	
A1	0.000	0.100	
A2	0.900	1.000	
b	0.200	0.400	
С	0.080	0.150	
D	2.000	2.200	
E	1.150	1.350	
E1	2.150	2.450	
е	0.650 TYP.		
e1	1.200	1.400	
L	0.525 REF.		
L1	0.260	0.460	
θ	0°	8°	

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 2SB1204S-TL-E
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